

Notice of References Cited

Application/Control No.

09/233,377

Applicant(s)/Patent Under
Reexamination
SANDHU ET AL.

Examiner

Thanhha Pham

Art Unit

2813

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*		Document Number	Date	Name	Classification	
		Country Code-Number-Kind Code	MM-YYYY			
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	B	US-5,608,266-	03-1997	Agnello et al	257	768
	C	US-5,828,131-	10-1998	Cabral et al	257	757
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	K	US- -				
	L	US- -				
	M	US- -				

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		Country Code-Number-Kind Code	MM-YYYY				
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NON-PATENT DOCUMENTS

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	U	Huang et al, "The Influence of Ge-implantation on the electrical characteristics of the Ultra-Shallow Junction Formed by Using Silicide as a diffusion", IEEE Electron Device Letters, Vol 17 Issue 3, March 1996, pp 88-90.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.